

# Thin-Film BAW Resonator with Equivalent Circuit

This tutorial demonstrates how to

- I Model a thin-film BAW resonator
- **2** Set up an equivalent-circuit model with lumped parameters
- 3 Determine the values of the lumped parameters using a Parameter Estimation Study

The tutorial outlines the steps from FEM modeling to deriving a compact circuit model for system-level simulations.

# From FEM to Lumped Parameter Model

While FEM can compute eigenfrequencies, eigenmodes, and frequency responses, extending the method to model complex circuits would be computationally costly and inefficient. In circuit design, components are represented by equivalent circuits with lumped parameters. In this tutorial you will create a FEM model of an FBAR in 3D and derive its equivalent circuit model based on the FEM simulation and a Parameter Estimation Study. The FBAR is a building block in circuits used in mobile devices.

# Model Definition

# FEM Model of the FBAR

The model is based on a five-sided apodized FBAR design for maximizing confinement of vibrational energy. The device is suspended from the anchor points. More information on the structure and operation of such a resonator can be found in the Thin-Film BAW Composite Resonator model documentation. In this tutorial, the FBAR geometry is parameterized following the first table in the Modeling Instructions section. Because of the symmetry of the device structure and the mode of interest, only a 36-degree sector needs to be modeled (see Figure 1), which reduces the computational time significantly. This is a good strategy to use in this particular model where a fine mesh is needed to compute the eigenfrequency and to generate a smooth surface plot of the mode shape. The FBAR is designed to have a series resonance at about 3.25 GHz and comprises a stack of a 0.2 μm silicon nitride supporting layer, a 0.1 μm molybdenum bottom electrode, a 1 μm aluminum nitride piezoelectric layer, and a 0.2 μm aluminum top electrode. The FEM model is used to compute the frequency response of the device using a Frequency Domain study. In the following steps, this FEM data is used as reference or the Experimental data.

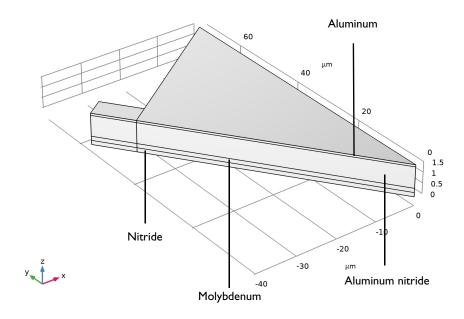


Figure 1: 36-degree sector of the five-sided thin-film BAW resonator.

The Modified Butterworth-Van Dyke Equivalent Circuit Model

An electromechanical device such as the FBAR can be represented by the Modified Butterworth-Van Dyke circuit with six lumped elements illustrated in Figure 2. The circuit is essentially the aluminum nitride capacitance Co in parallel with the series circuit Rm-Lm-Cm (the motional branch) for the piezoelectric effect. The Electrical Circuit interface is used to specify and excite the circuit using the initial values listed in Table 1. These values are estimated using equations in Ref. 1 and are based on the resonance and antiresonance frequencies of the FEM model and the Co value from the device geometry. As in the FEM model, the circuit model is used to compute the frequency response of the device using a Frequency Domain study. With the appropriate initial values, the frequency response from FEM and the circuit model should be close.

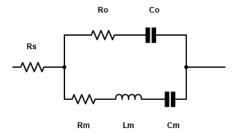


Figure 2: Diagram of the mBVD circuit model.

TABLE I: INITIAL VALUES USED IN THE CIRCUIT SIMULATION.

Parameter	Value
Cm	62 fF
Lm	39 nH
Со	I pF
Rs	ΙΩ
Ro	500 Ω
Rm	ΙΩ

# Parameter Estimation Study

To derive the precise values of the model parameters, use a Parameter Estimation study. In the Parameter Estimation study, a model expression is computed from the Frequency Domain study of the circuit model defined by the six parameters, which are varied to fit the experimental data (from FEM). To fit the model expression to the experimental data, Parameter Estimation minimizes an objective function defined as the error between model expression and experimental data. The output of the Parameter Estimation (PE) is the set of circuit parameters that best approximates the frequency response from FEM.

# Results and Discussion

Figure 3 shows the absolute value of the terminal current as a function of frequency from the Frequency Domain study between 2.8 and 3.8 GHz. The series resonance frequency at 3.25 GHz corresponds to the thickness-extension mode.

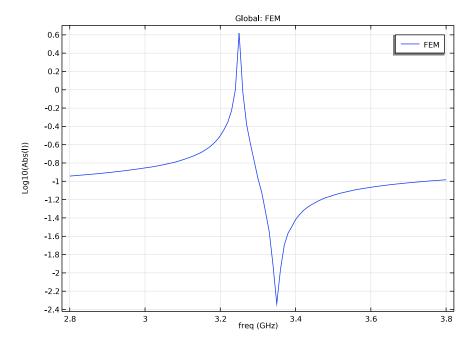


Figure 3: Plot of current versus frequency from FEM simulation showing series resonance at 3.25 GHz of the thickness-extension mode.

A second Frequency Domain study analyzes the frequency response of the circuit as defined by parameter initial values listed in Table 1. Figure 4 shows the plot for the circuit simulation superimposed onto the plot from the FEM simulation.

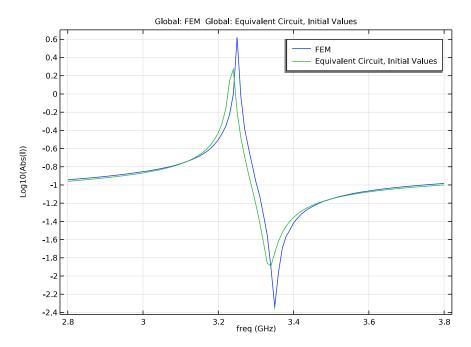


Figure 4: Plot of current versus frequency from FEM simulation and circuit simulation using the parameter initial values.

Figure 5 shows the output of the Parameter Estimation study comparison between experimental data and model expression. The fitted parameters are listed in Table 2.

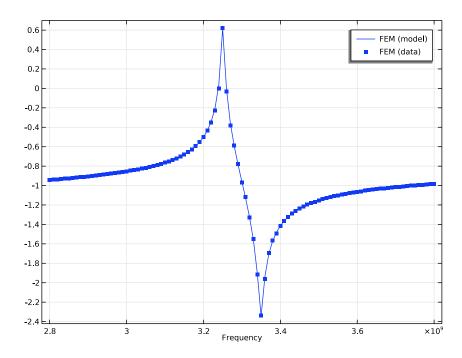


Figure 5: Plot of FEM result and equivalent circuit using final parameters from the Parameter Estimation Study.

TABLE 2: VALUES OF CIRCUIT PARAMETERS COMPUTED FROM PARAMETER ESTIMATION STUDY.

Parameter	Value
Cm	64.49 fF
Lm	37.18 nH
Со	1.04 pF
Rs	0.87 Ω
Ro	1340 Ω
Rm	0.325 Ω

Figure 6 is a surface plot of the solid displacement and the shape of the thickness-extension mode.

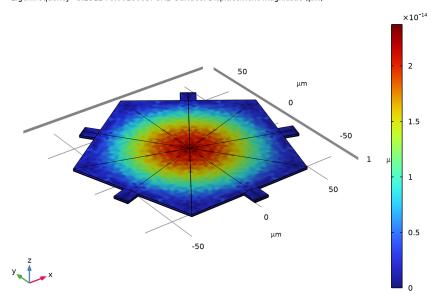


Figure 6: Surface plot showing the pattern of displacement for the thickness-extension mode.

Figure 6 shows the mode shape at 3.25 GHz from the FEM Eigenfrequency study. For high-resonance devices, an Eigenfrequency study often returns many solutions that are very close to the resonance frequency at 3.25 GHz. These are called spurious modes and need to be discarded based on visual inspection. As an alternative to visual verification, you can compute the displacement phase uniformity and plot against frequency. For the true resonance the value will be close to 1 whereas for spurious modes, they will be much smaller than 1. A plot of displacement phase uniformity versus frequency is shown in Figure 7.

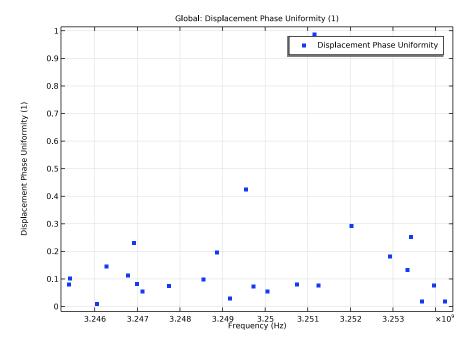


Figure 7: Plot of displacement phase uniformity versus frequency. Its value is close to 1 only at the resonance frequency of 3.25 GHz.

# References

1. J. D. Larson, P. D. Bradley, S. Wartenberg and R. C. Ruby, "Modified Butterworth-Van Dyke circuit for FBAR resonators and automated measurement system," *Proc. IEEE Ultrason. Symp.*, pp. 863–868, 2000.

**Application Library path:** MEMS\_Module/Piezoelectric\_Devices/thin\_film\_baw\_resonator\_3d\_equivalent\_circuit

From the File menu, choose New.

#### NEW

In the New window, click Model Wizard.

# MODEL WIZARD

- I In the Model Wizard window, Start by creating a new 3D model with a Piezoelectricity multiphysics interface.
- 2 click **1 3D**.
- 3 In the Select Physics tree, select AC/DC>Electromagnetics and Mechanics>Piezoelectricity> Piezoelectricity, Solid.
- 4 Click Add.
- 5 Click Study.
- 6 In the Select Study tree, select General Studies>Frequency Domain.
- 7 Click M Done.

# GEOMETRY I

Use microns to define the geometry unit.

- I In the Model Builder window, under Component I (compl) click Geometry I.
- 2 In the Settings window for Geometry, locate the Units section.
- 3 From the Length unit list, choose  $\mu m$ .

Define and specify the parameters for the FEM model.

# **GLOBAL DEFINITIONS**

Parameters - FEM Model

- I In the Model Builder window, under Global Definitions click Parameters I.
- 2 In the Settings window for Parameters, type Parameters FEM Model in the Label text field.

**3** Locate the **Parameters** section. In the table, enter the following settings:

Name	Expression	Value	Description
L	85[um]	8.5E-5 m	Length of resonator side
L_a	10[um]	IE-5 m	Length of anchor
W_a	10[um]	IE-5 m	Width of anchor
t_te	O.1[um]	1E-7 m	Thickness of top electrode
t_piezo	1 [ um ]	IE-6 m	Thickness of piezoelectric layer
t_be	0.2[um]	2E-7 m	Thickness of bottom electrode
t_nitride	0.2[um]	2E-7 m	Thickness of nitride membrane
Vapp	5[V]	5 V	Applied voltage
L_apo	L/(2*tan(36[deg]))	5.8496E-5 m	Apothem of pentagon

Define and specify the parameters for the circuit model.

# Parameters - Equivalent Circuit Model

- I In the Home toolbar, click Pi Parameters and choose Add>Parameters.
- 2 In the Settings window for Parameters, type Parameters Equivalent Circuit Model in the Label text field.
- **3** Locate the **Parameters** section. In the table, enter the following settings:

Name	Expression	Value	Description
Cm	62[fF]	6.2E-14 F	Capacitor, motional
Lm	39[nH]	3.9E-8 H	Inductor, motional
Rm	1[ohm]	ΙΩ	Resistor, motional
Co	1[pF]	1E-12 F	Capacitor
Ro	500[ohm]	500 Ω	Resistor
Rs	1[ohm]	ΙΩ	Resistor
Vsrc	5[V]	5 V	Voltage Source

Create the geometry model of a 36-degree sector of the resonator.

#### **GEOMETRY I**

Work Plane I (wpl)

In the Geometry toolbar, click Work Plane.

Work Plane I (wp I)>Plane Geometry

In the Model Builder window, click Plane Geometry.

Work Plane I (wbl)>Square I (sql)

- I In the Work Plane toolbar, click Square.
- 2 In the Settings window for Square, locate the Size section.
- 3 In the Side length text field, type L apo.

Work Plane I (wp I)>Square 2 (sq2)

- I In the Work Plane toolbar, click Square.
- 2 In the Settings window for Square, locate the Size section.
- 3 In the Side length text field, type 2\*L.
- 4 Locate the Rotation Angle section. In the Rotation text field, type -36.

Work Plane I (wp I)>Difference I (dif I)

- I In the Work Plane toolbar, click | Booleans and Partitions and choose Difference.
- **2** Select the object **sql** only.
- 3 In the Settings window for Difference, locate the Difference section.
- 4 Click to select the **Activate Selection** toggle button for **Objects to subtract**.
- **5** Select the object **sq2** only.

Work Plane I (wp I)>Rectangle I (r I)

- I In the Work Plane toolbar, click Rectangle.
- 2 In the Settings window for Rectangle, locate the Size and Shape section.
- 3 In the Width text field, type W a/2.
- 4 In the **Height** text field, type L\_a.
- **5** Locate the **Position** section. In the **yw** text field, type L\_apo.

Work Plane I (wpl)>Rotate I (rotl)

- I In the Work Plane toolbar, click \( \sum\_{\text{transforms}} \) Transforms and choose Rotate.
- 2 In the Settings window for Rotate, locate the Rotation section.
- 3 In the Angle text field, type 36.
- 4 Click in the **Graphics** window and then press Ctrl+A to select both objects.

- 5 Click | Build Selected.
- 6 Click the **Zoom Extents** button in the **Graphics** toolbar.

# Extrude I (ext I)

- I In the Model Builder window, right-click Geometry I and choose Extrude.
- 2 In the Settings window for Extrude, locate the Distances section.
- **3** In the table, enter the following settings:

Distances (µm)
t_nitride
t_nitride+t_be
t_nitride+t_be+t_piezo
t_nitride+t_be+t_piezo+t_te

4 Click Pauld Selected.

Adjust the view scale in the z direction to better see the layers.

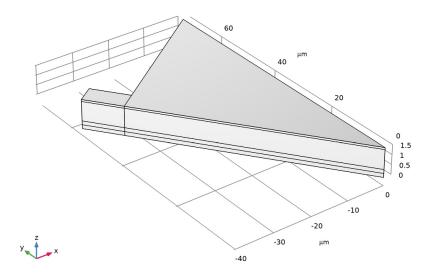
#### DEFINITIONS

In the Model Builder window, expand the Component I (compl)>Definitions node.

# Camera

- I In the Model Builder window, expand the Component I (compl)>Definitions>View I node, then click Camera.
- 2 In the Settings window for Camera, locate the Camera section.
- 3 From the View scale list, choose Manual.
- 4 In the z scale text field, type 5.

# 5 Click 🗘 Update.



Define selections for the piezoelectric, top, and bottom electrodes, and nitride layers as well as the symmetry and fixed boundaries. This will make specifying the materials and physics interfaces settings easier.

# Fixed

- I In the **Definitions** toolbar, click 堶 **Explicit**.
- 2 In the Settings window for Explicit, type Fixed in the Label text field.
- 3 Locate the Input Entities section. From the Geometric entity level list, choose Boundary.
- 4 Click Paste Selection.
- 5 In the Paste Selection dialog box, type 1 4 7 10 in the Selection text field.
- 6 Click OK.

# Nitride

- I In the **Definitions** toolbar, click 🔓 **Explicit**.
- 2 In the Settings window for Explicit, type Nitride in the Label text field.
- 3 Locate the Input Entities section. From the Geometric entity level list, choose Domain.
- 4 Click Paste Selection.
- 5 In the Paste Selection dialog box, type 1 5 in the Selection text field.

# 6 Click OK.

# Top Electrode

- I In the **Definitions** toolbar, click **\( \bigcap\_{\bigcap} \) Explicit**.
- 2 In the Settings window for Explicit, type Top Electrode in the Label text field.
- **3** Select Domains 4 and 8 only.

# Bottom Electrode

- I In the **Definitions** toolbar, click **\( \frac{1}{2} \) Explicit**.
- 2 In the Settings window for Explicit, type Bottom Electrode in the Label text field.
- **3** Select Domains 2 and 6 only.

# Piezoelectric

- I In the **Definitions** toolbar, click **\( \frac{1}{2} \) Explicit**.
- 2 In the Settings window for Explicit, type Piezoelectric in the Label text field.
- **3** Select Domains 3 and 7 only.

# Symmetry

- I In the **Definitions** toolbar, click **\( \bigcap\_{\bigcap} \) Explicit**.
- 2 In the Settings window for Explicit, type Symmetry in the Label text field.
- 3 Locate the Input Entities section. From the Geometric entity level list, choose Boundary.
- 4 Click Paste Selection.
- **5** In the **Paste Selection** dialog box, type 2 5 8 11 19 22 25 28 35 36 37 38 in the **Selection** text field.
- 6 Click OK.

Define an integration operator for evaluation of the displacement.

# Integration | (intob|)

- I In the **Definitions** toolbar, click Nonlocal Couplings and choose Integration.
- 2 In the Settings window for Integration, locate the Source Selection section.
- 3 From the Geometric entity level list, choose Boundary.
- 4 Click Paste Selection.
- 5 In the Paste Selection dialog box, type 30 in the Selection text field.
- 6 Click OK.

Specify the settings for the **Electrostatics** interface.

# **ELECTROSTATICS (ES)**

Charge Conservation, Piezoelectric 1

- I In the Model Builder window, under Component I (compl)>Electrostatics (es) click Charge Conservation, Piezoelectric I.
- 2 In the Settings window for Charge Conservation, Piezoelectric, locate the Domain Selection section.
- 3 From the Selection list, choose Piezoelectric.

# Symmetry Plane 1

- I In the Physics toolbar, click **Boundaries** and choose Symmetry Plane.
- 2 In the Settings window for Symmetry Plane, locate the Boundary Selection section.
- **3** From the **Selection** list, choose **Symmetry**.

# Tob Terminal

- I In the Physics toolbar, click **Domains** and choose Terminal.
- 2 In the Settings window for Terminal, type Top Terminal in the Label text field.
- 3 Locate the **Domain Selection** section. From the **Selection** list, choose **Top Electrode**.
- 4 Locate the Terminal section. From the Terminal type list, choose Voltage.
- **5** In the  $V_0$  text field, type Vapp.

# Ground I

- I In the Physics toolbar, click **Boundaries** and choose **Ground**.
- 2 In the Settings window for Ground, locate the Boundary Selection section.
- 3 Click Paste Selection.
- 4 In the Paste Selection dialog box, type 9 26 in the Selection text field.
- 5 Click OK.

Specify the settings for the **Solid Mechanics** interface.

# SOLID MECHANICS (SOLID)

Linear Elastic Material I

In the Model Builder window, under Component I (compl)>Solid Mechanics (solid) click Linear Elastic Material I.

#### Dambing 1

- I In the Physics toolbar, click 🕞 Attributes and choose Damping.
- 2 In the Settings window for Damping, locate the Damping Settings section.

3 From the Damping type list, choose Isotropic loss factor.

Piezoelectric Material I

- I In the Model Builder window, under Component I (compl)>Solid Mechanics (solid) click Piezoelectric Material I.
- 2 In the Settings window for Piezoelectric Material, locate the Domain Selection section.
- 3 From the Selection list, choose Piezoelectric.

Mechanical Damping I

In the Physics toolbar, click 🦳 Attributes and choose Mechanical Damping.

Fixed Constraint I

- I In the Physics toolbar, click **Boundaries** and choose Fixed Constraint.
- 2 In the Settings window for Fixed Constraint, locate the Boundary Selection section.
- 3 From the Selection list, choose Fixed.

Symmetry I

- I In the Physics toolbar, click **Boundaries** and choose Symmetry.
- 2 In the Settings window for Symmetry, locate the Boundary Selection section.
- 3 From the Selection list, choose Symmetry.

Create the mesh for the model.

# MESH I

Free Triangular I

- I In the Mesh toolbar, click More Generators and choose Free Triangular.
- 2 In the Settings window for Free Triangular, locate the Boundary Selection section.
- 3 Click Paste Selection.
- 4 In the Paste Selection dialog box, type 12 29 in the Selection text field.
- 5 Click OK.

Size 1

- I Right-click Free Triangular I and choose Size.
- 2 In the Settings window for Size, locate the Element Size section.
- 3 From the Predefined list, choose Extra fine.

Swept I

In the Mesh toolbar, click A Swept.

# Distribution 1

- I Right-click Swept I and choose Distribution.
- 2 In the Settings window for Distribution, locate the Domain Selection section.
- 3 From the Selection list, choose Piezoelectric.
- 4 Locate the Distribution section. In the Number of elements text field, type 3.

#### Distribution 2

- I In the Model Builder window, right-click Swept I and choose Distribution.
- 2 In the Settings window for Distribution, locate the Domain Selection section.
- **3** From the **Selection** list, choose **Nitride**.
- 4 Locate the Distribution section. In the Number of elements text field, type 2.

# Distribution 3

- I Right-click Swept I and choose Distribution.
- 2 In the Settings window for Distribution, locate the Domain Selection section.
- **3** From the **Selection** list, choose **Bottom Electrode**.
- 4 Locate the Distribution section. In the Number of elements text field, type 2.

#### Distribution 4

- I Right-click Swept I and choose Distribution.
- 2 In the Settings window for Distribution, locate the Domain Selection section.
- **3** From the **Selection** list, choose **Top Electrode**.
- 4 Locate the Distribution section. In the Number of elements text field, type 1.
- 5 Click **Build All**.

# MATERIALS

Add materials to the model and specify the regions they belong to.

#### ADD MATERIAL

- I In the Home toolbar, click **Add Material** to open the Add Material window.
- 2 Go to the Add Material window.
- 3 In the tree, select Piezoelectric>Aluminum Nitride.
- 4 Click Add to Component in the window toolbar.

#### MATERIALS

Aluminum Nitride (mat I)

- I In the Settings window for Material, locate the Geometric Entity Selection section.
- **2** From the **Selection** list, choose **Piezoelectric**.
- **3** Locate the **Material Contents** section. In the table, enter the following settings:

Property	Variable	Value	Unit	Property group
Loss factor for elasticity matrix cE	eta_cE_iso; eta_cEii = eta_cE_iso, eta_cEij = 0	1e-3	I	Stress-charge form

# ADD MATERIAL

- I Go to the Add Material window.
- 2 In the tree, select MEMS>Metals>Al Aluminum.
- 3 Click Add to Component in the window toolbar.

#### MATERIALS

AI - Aluminum (mat2)

- I In the Settings window for Material, locate the Geometric Entity Selection section.
- 2 From the Selection list, choose Top Electrode.
- **3** Locate the **Material Contents** section. In the table, enter the following settings:

Property	Variable	Value	Unit	Property group
Isotropic structural loss	eta_s	1e-4	1	Basic
factor				

#### ADD MATERIAL

- I Go to the Add Material window.
- 2 In the tree, select Built-in>Molybdenum.
- 3 Click Add to Component in the window toolbar.

# MATERIALS

Molybdenum (mat3)

- I In the Settings window for Material, locate the Geometric Entity Selection section.
- 2 From the Selection list, choose Bottom Electrode.

3 Locate the Material Contents section. In the table, enter the following settings:

Property	Variable	Value	Unit	Property group
Relative permittivity	epsilonr_iso; epsilonrii = epsilonr_iso, epsilonrij = 0	1	I	Basic
Isotropic structural loss factor	eta_s	1e-4	1	Basic

#### ADD MATERIAL

- I Go to the Add Material window.
- 2 In the tree, select MEMS>Insulators>Si3N4 Silicon nitride.
- 3 Click Add to Component in the window toolbar.
- 4 In the Home toolbar, click 4 Add Material to close the Add Material window.

#### MATERIALS

Si3N4 - Silicon nitride (mat4)

- I In the Settings window for Material, locate the Geometric Entity Selection section.
- 2 From the Selection list, choose Nitride.
- 3 Locate the Material Contents section. In the table, enter the following settings:

Property	Variable	Value	Unit	Property group
Isotropic structural loss factor	eta_s	1e-2	I	Basic

Set up a Frequency Domain study for the FEM model. The range is chosen to include the features of interest: the series and parallel resonance frequencies. Also, disable the generation of default plots from this study.

# FREQUENCY DOMAIN - FEM

- I In the Model Builder window, click Study I.
- 2 In the Settings window for Study, type Frequency Domain FEM in the Label text field.
- 3 Locate the Study Settings section. Clear the Generate default plots check box.

Step 1: Frequency Domain

I In the Model Builder window, under Frequency Domain - FEM click Step 1: Frequency Domain.

- 2 In the Settings window for Frequency Domain, locate the Study Settings section.
- 3 From the Frequency unit list, choose GHz.
- 4 In the Frequencies text field, type range (2.8, 0.01, 3.8).
- 5 In the Home toolbar, click **Compute**.

From the FEM simulation in Study 1, plot the terminal current versus frequency.

#### RESULTS

# Frequency Response

- I In the Home toolbar, click Add Plot Group and choose ID Plot Group.
- 2 In the Settings window for ID Plot Group, type Frequency Response in the Label text field.
- 3 Locate the Plot Settings section.
- 4 Select the y-axis label check box. In the associated text field, type Log10(Abs(I)).

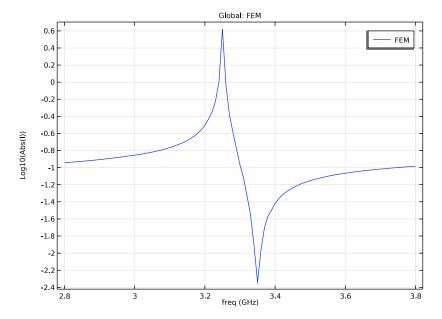
Because the 36 degree sector model is 1/10 of the device geometry, multiply terminal current by a factor of 10.

# FEM

- I Right-click Frequency Response and choose Global.
- 2 In the Settings window for Global, type FEM in the Label text field.
- 3 Locate the y-Axis Data section. In the table, enter the following settings:

Expression	Unit	Description
log10(abs(10*es.IO_1))		FEM

4 In the Frequency Response toolbar, click Plot.



Add an Electrical Circuit interface. Add the components of the equivalent circuit and specify their parameter values.

# ADD PHYSICS

- I In the Home toolbar, click open the Add Physics window.
- 2 Go to the Add Physics window.
- 3 In the tree, select AC/DC>Electrical Circuit (cir).
- 4 Click Add to Component I in the window toolbar.
- 5 In the Home toolbar, click and Physics to close the Add Physics window.

# ELECTRICAL CIRCUIT (CIR)

Voltage Source I (VI)

- I Right-click Component I (compl)>Electrical Circuit (cir) and choose Voltage Source.
- 2 In the Settings window for Voltage Source, locate the Node Connections section.

**3** In the table, enter the following settings:

Label	Node names
n	0

4 Locate the Device Parameters section. In the  $v_{
m src}$  text field, type Vsrc.

R\_s

- I In the Electrical Circuit toolbar, click Resistor.
- 2 In the Settings window for Resistor, type R s in the Label text field.
- **3** Locate the **Node Connections** section. In the table, enter the following settings:

Label	Node names
Р	1
n	2

4 Locate the **Device Parameters** section. In the R text field, type Rs.

R m

- I In the Electrical Circuit toolbar, click Resistor.
- 2 In the Settings window for Resistor, type R\_m in the Label text field.
- **3** Locate the **Node Connections** section. In the table, enter the following settings:

Label	Node names
P	2
n	3

**4** Locate the **Device Parameters** section. In the R text field, type Rm.

L m

- I In the Electrical Circuit toolbar, click OOO Inductor.
- 2 In the Settings window for Inductor, type L m in the Label text field.
- **3** Locate the **Node Connections** section. In the table, enter the following settings:

Label	Node names
Р	3
n	4

4 Locate the **Device Parameters** section. In the L text field, type Lm.

C m

- I In the Electrical Circuit toolbar, click → Capacitor.
- 2 In the Settings window for Capacitor, type C\_m in the Label text field.
- **3** Locate the **Node Connections** section. In the table, enter the following settings:

Label	Node names
P	4
n	0

**4** Locate the **Device Parameters** section. In the C text field, type Cm.

Ro

- I In the Electrical Circuit toolbar, click Resistor.
- 2 In the Settings window for Resistor, type R o in the Label text field.
- **3** Locate the **Node Connections** section. In the table, enter the following settings:

Label	Node names
Р	2
n	0

**4** Locate the **Device Parameters** section. In the R text field, type Ro.

 $C_0$ 

- I In the Electrical Circuit toolbar, click ⊢⊢ Capacitor.
- 2 In the Settings window for Capacitor, type C\_0 in the Label text field.
- **3** Locate the **Node Connections** section. In the table, enter the following settings:

Label	Node names
Р	2
n	0

**4** Locate the **Device Parameters** section. In the C text field, type Co.

Set up a Frequency Domain study for the circuit model. Disable the Electrostatics and Solid **Mechanics** interfaces and the **Piezoelectricity** multiphysics coupling. Also, disable generation of default plots.

# ADD STUDY

I In the Home toolbar, click Add Study to open the Add Study window.

- **2** Go to the **Add Study** window.
- 3 Find the Studies subsection. In the Select Study tree, select General Studies> Frequency Domain.
- 4 Click Add Study in the window toolbar.
- 5 In the Home toolbar, click Add Study to close the Add Study window.

# FREQUENCY DOMAIN - EQUIVALENT CIRCUIT

- I In the Model Builder window, click Study 2.
- 2 In the Settings window for Study, type Frequency Domain Equivalent Circuit in the Label text field.

# Step 1: Frequency Domain

- I In the Model Builder window, under Frequency Domain Equivalent Circuit click
  Step 1: Frequency Domain.
- 2 In the Settings window for Frequency Domain, locate the Study Settings section.
- **3** From the **Frequency unit** list, choose **GHz**.
- 4 In the Frequencies text field, type range (2.8,0.01,3.8).
- 5 Locate the Physics and Variables Selection section. In the table, clear the Solve for check boxes for Electrostatics (es) and Solid Mechanics (solid).
- 6 In the table, clear the Solve for check box for Piezoelectricity I (pzel).
- 7 In the Model Builder window, click Frequency Domain Equivalent Circuit.
- 8 In the Settings window for Study, locate the Study Settings section.
- **9** Clear the **Generate default plots** check box.
- **10** In the **Home** toolbar, click **Compute**.

From the circuit simulation in Study 2, plot the terminal current versus frequency and add to the **Frequency Domain** plot group to compare the FEM and equivalent-circuit results using initial values of the circuit parameters.

#### RESULTS

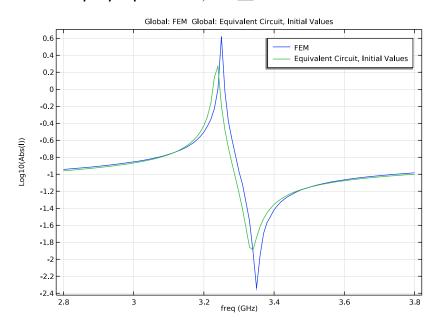
Equivalent Circuit, Initial Values

- I In the Model Builder window, right-click Frequency Response and choose Global.
- 2 In the Settings window for Global, type Equivalent Circuit, Initial Values in the Label text field.
- 3 Locate the Data section. From the Dataset list, choose Frequency Domain Equivalent Circuit/Solution 2 (sol2).

4 Locate the y-Axis Data section. In the table, enter the following settings:

Expression	Unit	Description
log10(abs(cir.R1_i))		Equivalent Circuit, Initial Values

5 In the Frequency Response toolbar, click Plot.



Copy the result of Study 1 to a table for use as reference data in a Parameter Estimation study.

# FEM

In the Model Builder window, right-click FEM and choose Copy Plot Data to Table.

# FEM Reference Data

- I In the Model Builder window, under Results>Tables click Table I.
- 2 In the Settings window for Table, type FEM Reference Data in the Label text field.
- 3 Click ( Update.

Set up a Parameter Estimation study based on the previous Frequency Domain study for the circuit model.

# ADD STUDY

I In the Home toolbar, click Add Study to open the Add Study window.

- **2** Go to the **Add Study** window.
- 3 Find the Studies subsection. In the Select Study tree, select Empty Study.
- 4 Click Add Study in the window toolbar.
- 5 In the Home toolbar, click Add Study to close the Add Study window.

#### PARAMETER EXTRACTION

In the Settings window for Study, type Parameter Extraction in the Label text field.

# FREQUENCY DOMAIN - EQUIVALENT CIRCUIT

Step 1: Frequency Domain

In the Model Builder window, under Frequency Domain - Equivalent Circuit right-click **Step 1: Frequency Domain** and choose **Copy**.

# PARAMETER EXTRACTION

In the Model Builder window, right-click Parameter Extraction and choose Paste Frequency Domain.

Parameter Estimation

- I In the Study toolbar, click optimization and choose Parameter Estimation. Define the Experimental Data for the Parameter Estimation study.
- 2 In the Settings window for Parameter Estimation, locate the Experimental Data section.
- 3 From the Data source list, choose Result table.
- 4 Locate the Data Column Settings section. In the table, enter the following settings:

Columns	Туре	Settings
freq (GHz)	Frequency	Frequency unit=GHz

5 From the Frequency unit list, choose GHz.

Next, define the Model expression to be computed by the Frequency Domain - Equivalent **Circuit** study.

- **6** In the table, click to select the cell at row number 2 and column number 2.
- 7 In the Model expression text field, type log10(abs(comp1.cir.R1 i)).
- **8** In the **Unit** text field, type 1.
- 9 From the Scale list, choose Manual.

10 In the Scale value text field, type 1.

Select the circuit parameters to be included in the study. Specify their initial values, scaling, and the lower and upper bounds. For this study, a default plot will be generated automatically comparing the FEM reference data and the circuit model using the final values of the circuit parameters.

II Locate the Estimated Parameters section. Click + Add six times.

12 In the table, enter the following settings:

Parameter name	Initial value	Scale	Lower bound	Upper bound
Cm (Capacitor, motional)	62[fF]	60[fF]	45[fF]	75[fF]
Lm (Inductor, motional)	39[nH]	40[nH]	10[nH]	70[nH]
Co (Capacitor)	1[pF]	1[pF]	0.1[pF]	2[pF]
Rs (Resistor)	1[ohm]	10[ohm]	0.001[ohm]	20[ohm]
Rm (Resistor, motional)	1[ohm]	10[ohm]	0.01[ohm]	20[ohm]
Ro (Resistor)	500[ohm]	2500[ohm]	100[ohm]	5000[ohm]

13 Locate the Parameter Estimation Method section. From the Method list, choose SNOPT.

14 Find the Solver settings subsection. From the Least-squares time/parameter method list, choose Use only least-squares data points.

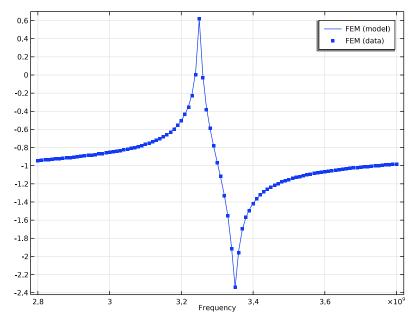
Because in the Frequency Domain the variables are complex, the option for Split complex variables in real and imaginary parts must be enabled.

Solution 3 (sol3)

- I In the Study toolbar, click Show Default Solver.
- 2 In the Model Builder window, expand the Solution 3 (sol3) node, then click Compile Equations: Frequency Domain.
- 3 In the Settings window for Compile Equations, locate the Study and Step section.
- 4 Select the Split complex variables in real and imaginary parts check box.
- 5 In the Study toolbar, click **Compute**.

#### RESULTS

Parameter estimation



Set up an **Eigenfrequency** study to search for an eigenfrequency around 3.25 GHz. Deselect the **Electrical Circuit** interface from the list of physics interfaces solved for.

# ADD STUDY

- I In the Study toolbar, click Add Study to open the Add Study window.
- 2 Go to the Add Study window.
- 3 Find the Studies subsection. In the Select Study tree, select Preset Studies for Selected Multiphysics>Eigenfrequency.
- 4 Click Add Study in the window toolbar.
- 5 In the Study toolbar, click Add Study to close the Add Study window.

# STUDY 4

# Step 1: Eigenfrequency

- I In the Settings window for Eigenfrequency, locate the Study Settings section.
- 2 Select the **Desired number of eigenfrequencies** check box. In the associated text field, type 25.

- 3 Find the Elliptic search region subsection. From the Unit list, choose GHz.
- 4 In the Search for eigenfrequencies around shift text field, type 3.25.
- 5 Locate the Physics and Variables Selection section. In the table, clear the Solve for check box for Electrical Circuit (cir).

Disable the generation of default plots from this **Eigenfrequency** study.

- 6 In the Model Builder window, click Study 4.
- 7 In the Settings window for Study, type Eigenfrequency in the Label text field.
- **8** Locate the **Study Settings** section. Clear the **Generate default plots** check box.
- 9 In the Study toolbar, click **Compute**.

Add a Mirror and a Sector dataset to complete the device structure. These datasets will be used in a plot from the Eigenfrequency study.

#### RESULTS

# Mirror 3D I

- I In the Results toolbar, click More Datasets and choose Mirror 3D.
- 2 In the Settings window for Mirror 3D, locate the Data section.
- 3 From the Dataset list, choose Eigenfrequency/Solution 4 (sol4).
- 4 Click Plot.

# Sector 3D I

- I In the Results toolbar, click More Datasets and choose Sector 3D.
- 2 In the Settings window for Sector 3D, locate the Data section.
- 3 From the Dataset list, choose Mirror 3D 1.
- 4 Locate the Symmetry section. In the Number of sectors text field, type 5.
- 5 Click Plot.

From the **Eigenfrequency** study, create a 3D plot to show the shape of the eigenmode at 3.25 GHz. Use the dataset previously created.

# Modes

- I In the Results toolbar, click **a** 3D Plot Group.
- 2 In the Settings window for 3D Plot Group, type Modes in the Label text field.

# Surface 1

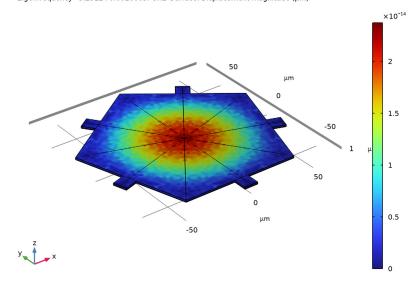
- I Right-click Modes and choose Surface.
- 2 In the Settings window for Surface, locate the Expression section.

- **3** In the **Expression** text field, type solid.disp.
- 4 Select the **Description** check box.

#### Modes

- I In the Model Builder window, click Modes.
- 2 In the Settings window for 3D Plot Group, locate the Data section.
- 3 From the Dataset list, choose Sector 3D 1.
- 4 In the Modes toolbar, click Plot.
- 5 From the Eigenfrequency (GHz) list, choose 3.2512+0.0016005i.
- 6 In the Modes toolbar, click Plot.

Eigenfrequency=3.2512+0.0016005i GHz Surface: Displacement magnitude (μm)



From the results of Study 1, evaluate the displacement phase uniformity. To do this, use the integral operator intop1 defined earlier to access the *z*-displacement at the top surface of the device.

# Displacement Phase Uniformity

- I In the Home toolbar, click Add Plot Group and choose ID Plot Group.
- 2 In the **Settings** window for **ID Plot Group**, type Displacement Phase Uniformity in the **Label** text field.
- 3 Locate the Data section. From the Dataset list, choose Eigenfrequency/Solution 4 (sol4).

# Global I

- I Right-click Displacement Phase Uniformity and choose Global.
- 2 In the Settings window for Global, locate the y-Axis Data section.
- **3** In the table, enter the following settings:

Expression	Unit	Description
<pre>abs(intop1(w))/intop1(abs(w))</pre>	1	Displacement Phase Uniformity

- 4 Locate the x-Axis Data section. From the Parameter list, choose Expression.
- 5 In the Expression text field, type freq.
- **6** In the **Displacement Phase Uniformity** toolbar, click  **Plot**.
- 7 Click to expand the Coloring and Style section. Find the Line style subsection. From the Line list, choose None.
- 8 Find the Line markers subsection. From the Marker list, choose Point.

